

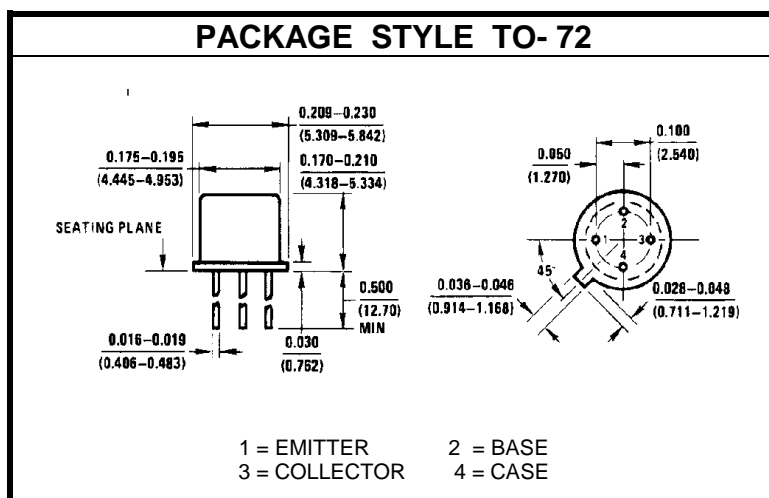
# NPN SILICON HIGH FREQUENCY TRANSISTOR

## DESCRIPTION:

The **2N3570** is Designed for High Frequency Low Noise Amplifier and Oscillator Applications.

## MAXIMUM RATINGS

$I_C$	50 mA
$V_{CB}$	30 V
$V_{CE}$	15 V
$V_{EB}$	3.0 V
$P_{DISS}$	200 mW @ $T_C = 25^\circ C$
$T_J$	$-65^\circ C$ to $+200^\circ C$
$T_{STG}$	$-65^\circ C$ to $+200^\circ C$
$\theta_{JC}$	500 $^\circ C/W$



## CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CEO}$	$I_C = 2 \text{ mA}$		15			V
$BV_{CBO}$	$I_C = 1.0 \mu A$		30			V
$I_{CBO}$	$V_{CB} = 6.0 \text{ V}$				10 1.0	$\mu A$
$T_A = 150^\circ C$						
$BV_{EBO}$	$I_E = 10 \mu A$		3.0			V
$h_{FE}$	$V_{CE} = 6.0 \text{ V}$	$I_C = 5.0 \text{ mA}$	20		150	---
$C_{ob}$	$V_{CB} = 6 \text{ V}$	$f = 1.0 \text{ MHz}$			0.75	pF
$h_{FE}$	$V_{CE} = 6 \text{ V}$	$I_C = 5 \text{ mA}$	20		150	---
$ h_{fe} $	$V_{CE} = 6 \text{ V}$	$I_C = 5 \text{ mA}$	3.75	4.25	6	---
$r_b \text{ } \dot{C}_C$	$V_{CB} = 6 \text{ V}$	$I_E = -5 \text{ mA}$	1	5	8	pF
$P_{osc}$	$V_{CC} = 20 \text{ V}$	$I_C = 15 \text{ mA}$		60		mW
$N_F$	$V_{CB} = 6 \text{ V}$	$I_C = 2 \text{ mA}$	$R_G = 50 \Omega$	6	7	dB